



General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low

$R_{DS(ON)}$.

Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Load Switch

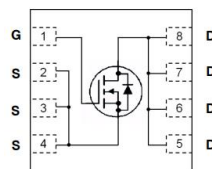
Ordering Information:

Part NO.	ZMSA009N08HG
Marking	ZMS009N08H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

Absolute Maximum Ratings $(T_C=25^{\circ}\text{C})$

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		80	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}\text{C}$	340	A
	I_D	$T_C=75^{\circ}\text{C}$	266	A
	I_D	$T_C=100^{\circ}\text{C}$	225	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^{\circ}\text{C}$;	1020	A
Total Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	188	W
Total Power Dissipation	P_D	$T_A=25^{\circ}\text{C}$	4.3	W
Operating Junction Temperature	T_J		-55 to +175	$^{\circ}\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^{\circ}\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	480	mJ
		$L=0.3\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	1008	mJ
ESD Level (HBM)	CLASS 2			

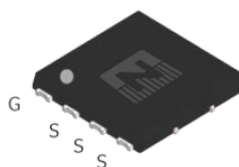
Product Summary



$V_{DS} = 80\text{V}$

$R_{DS(ON)} = 0.95\text{m}\Omega$

$I_D = 340\text{A}$



DFN8*8





•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.8	°C/W
Thermal resistance, junction-ambient ^②	R_{thJA}		-	35	°C/W
Soldering temperature	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=80V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$		0.95	1.15	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=20A$		60		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=30A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	13280	-	pF
Output capacitance	C_{oss}		-	9658	-	
Reverse transfer capacitance	C_{rss}		-	170	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=30A, V_{GS}=10V$	-	176	-	nC
Gate - Source charge	Q_{gs}		-	34	-	
Gate - Drain charge	Q_{gd}		-	33	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=30A$	-	35	-	ns
Turn-ON Rise time	t_r		-	18	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	74	-	ns
Turn-Off Fall time	t_f		-	23	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=50A$	-	96	-	ns
Reverse Recovery Charge	Q_{RR}		-	192	-	nC



Fig.1 Gate-Charge Characteristics

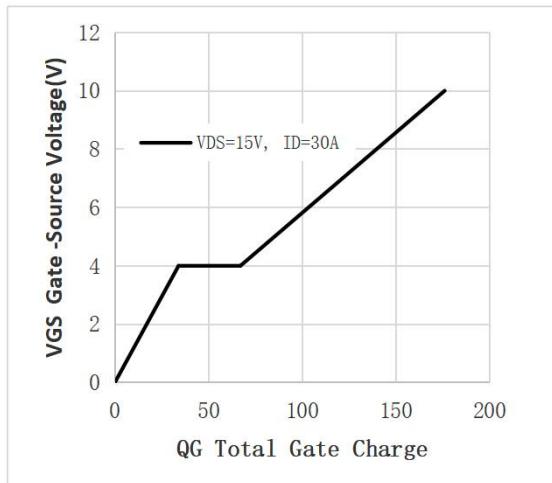


Fig.2 Capacitance Characteristics

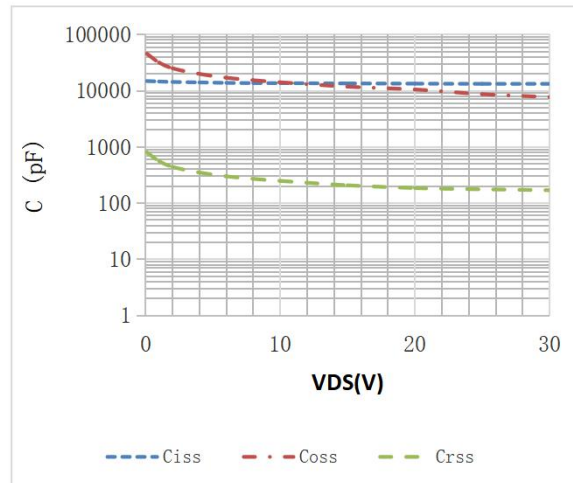


Fig.3 Power Dissipation

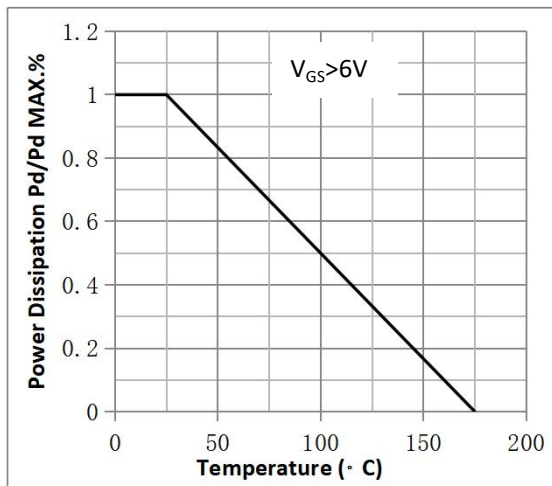


Fig.4 Typical output Characteristics

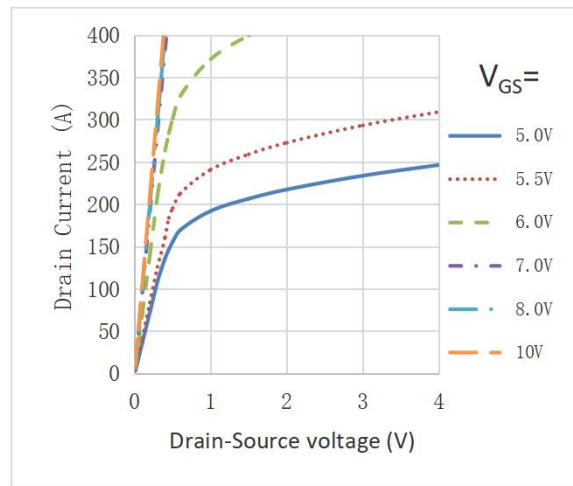


Fig.5 Threshold Voltage V.S Junction Temperature

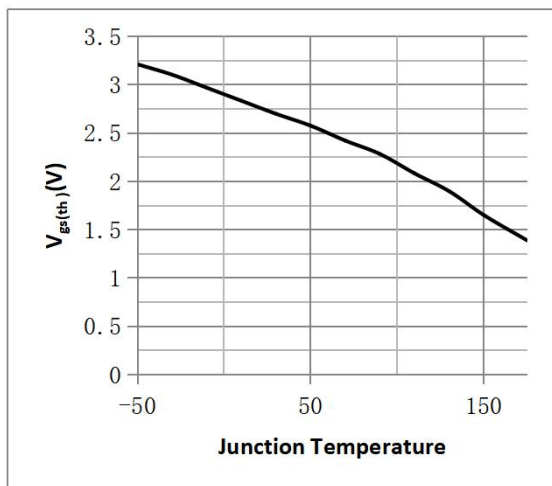


Fig.6 Resistance V.S Drain Current

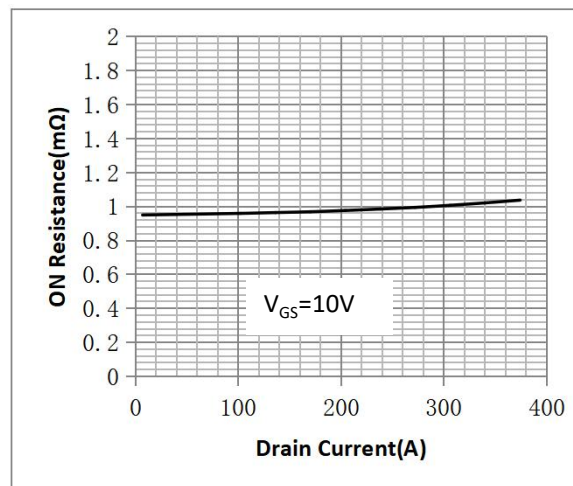




Fig.7 On-Resistance VS Gate Source Voltage

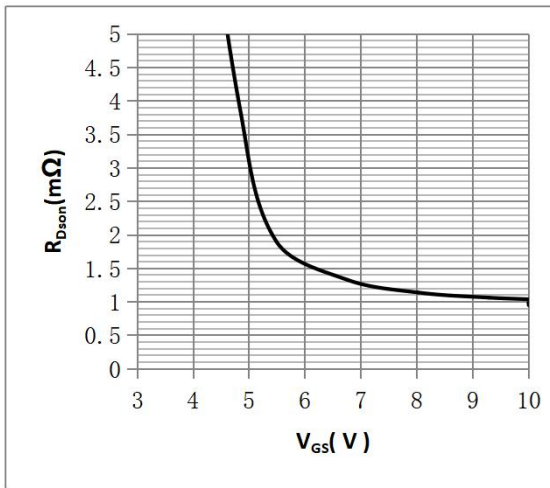


Fig.8 On-Resistance V.S Junction Temperature

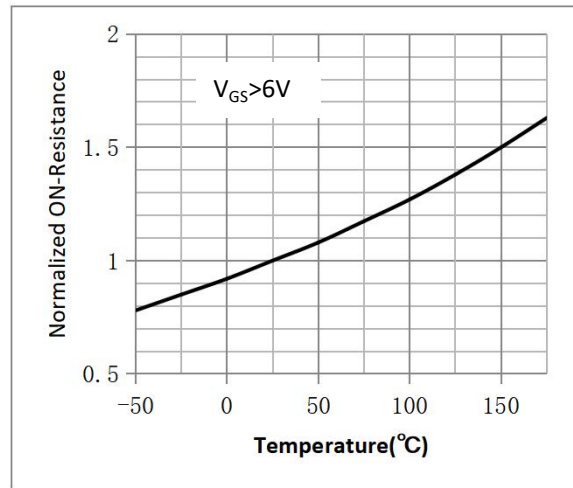


Figure 9. Diode Forward Voltage vs. Current

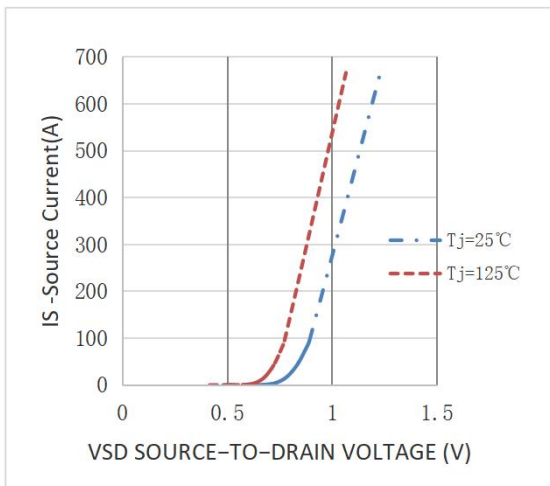


Figure 10. Transfer Characteristics

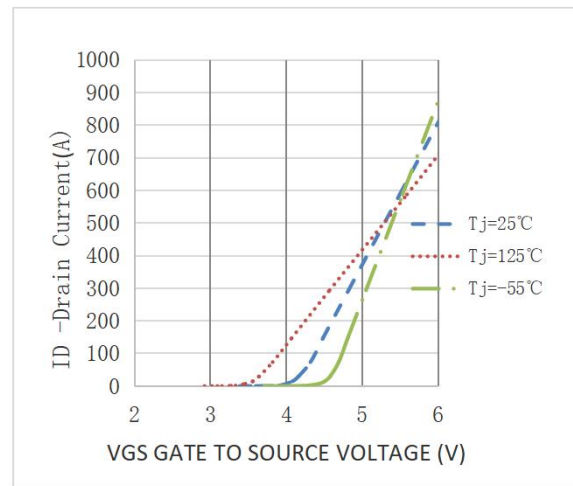
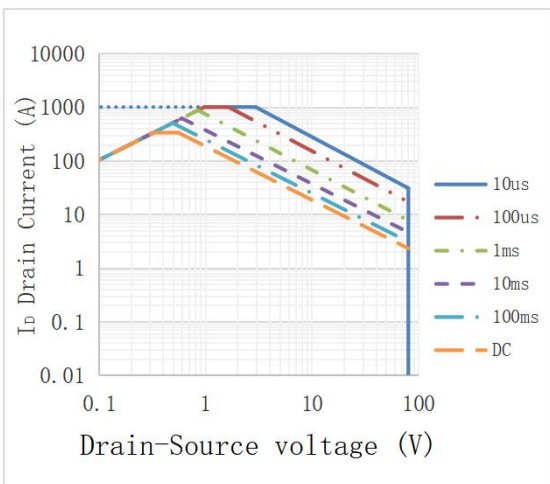
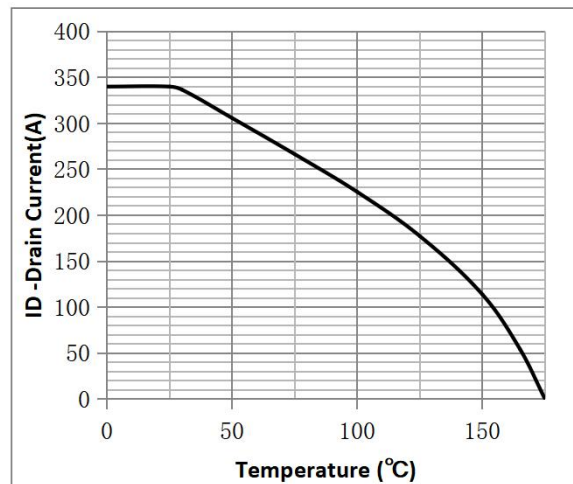
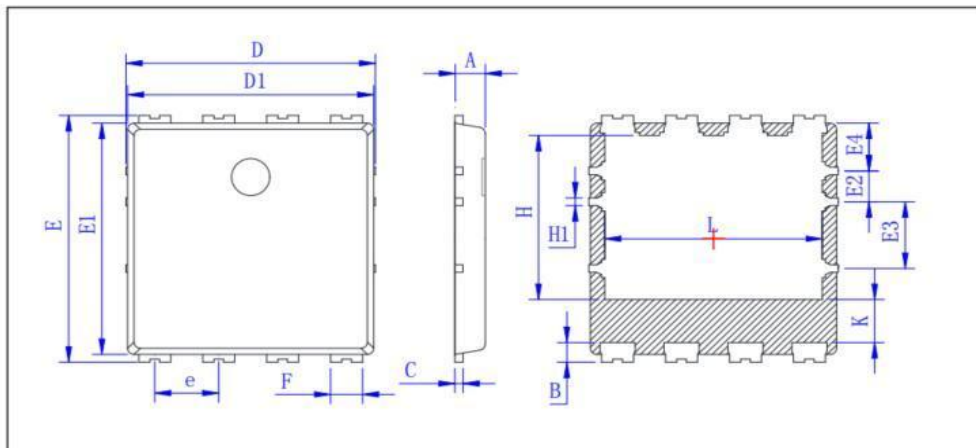


Fig.11 Safe Operating Area

Fig.12 ID vs. Case Temperature^③



•DFN8*8 Package Outline



Symbol	Min	Typ	Max
A	0.90	0.95	1.00
B	0.50	0.60	0.70
C	0.254 TYP		
D	7.70	7.80	7.90
D1	7.60	7.70	7.80
E	7.90	8.00	8.10
E1	7.40	7.50	7.60
E2	0.90	1.00	1.10
E3	2.06	2.16	2.26
E4	1.45	1.55	1.65
e	2.0 TYP		
F	1.00 TYP		
H	5.15	5.30	5.40
H1	0.20	0.25	0.35
L	6.60	6.80	6.90
K	1.20		



Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.7.6	new
B	2022.11.5	1.Add Reach,HF figure,2.ID figure modify 3.Rdson limit modify
C	2024.7.25	SOA curve Modified